

SILICON TRANSISTOR 2SB1578

PNP SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SB1578 features high current capacity in small dimension and is ideal for DC/DC converters and mortor drivers.

FEATURES

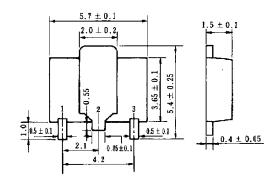
- New package with dimensions in between those of small signal and power signal package
- High current capacitance
- · Low collector saturation voltage
- · Complementary transistor with 2SD2425

QUALITY GRADES

Standard

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

PACKAGE DRAWING (UNIT: mm)



Electrode connection

- 1: Emitter
- 2: Collector
- 3: Base

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vcво		-60	V
Collector to emitter voltage	VCEO		-60	٧
Emitter to base voltage	VEBO		-6.0	٧
Collector current (DC)	Ic(DC)		-5.0	Α
Collector current (pulse)	IC(pulse)	PW ≤ 10 ms, duty cycle ≤ 50 %	-7.0	Α
Base current (DC)	I _{B(DC)}		-1.0	Α
Total power dissipation	Рт	$7.5~\text{cm}^2 \times 0.7~\text{mm}$ ceramic board used	2.0	W
Junction temperature	Tj		150	°C
Storage temperature	T _{stg}		−55 to +150	°C

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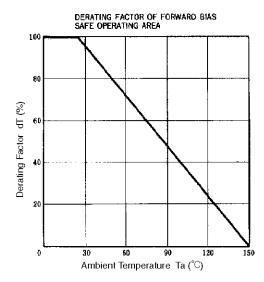
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

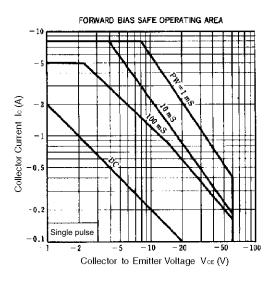
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vcb = -50 V, IE = 0			-10	μΑ
Emitter cutoff current	ІЕВО	V _{EB} = -6.0 V, Ic = 0			-10	μΑ
DC current gain	h _{FE1}	VcE = -1.0 V, Ic = -0.1 A	60	220		_
DC current gain	h _{FE2}	VcE = -1.0 V, Ic = -2.0 A	100	200	400	_
DC current gain	h _{FE3}	Vce = -2.0 V, Ic = -5.0 A	50	150		_
Collector saturation voltage	V _{CE(sat)}	Ic = -2.0 A, I _B = -0.2 A		-180	-300	mV
Base saturation voltage	V _{BE(sat)}	Ic = -2.0 A, I _B = -0.2 A		-0.9	-1.2	V
Turn-on time	ton	Ic = -2.0 A, Vcc = -10 V		0.6		μs
Storage time	t stg	$I_{B1} = -I_{B2} = -0.2 \text{ A}$ $R_L = 5.0 \Omega$		0.55		μs
Fall time	t _f	111 - 0.0 32		0.05		μs

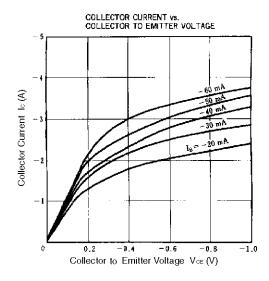
hfe CLASSIFICATION

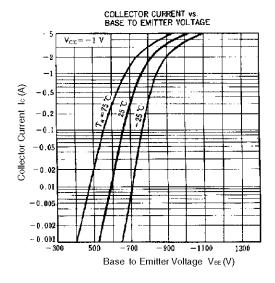
Marking	GB1	GB2	GB3	
h _{FE2}	100 to 200	160 to 320	200 to 400	

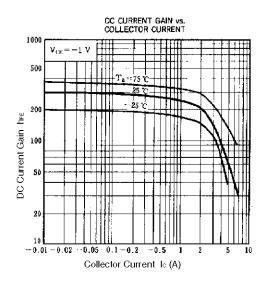
TYPICAL CHARACTERISTICS (Ta = 25°C)

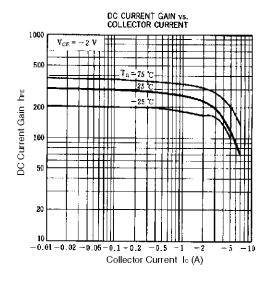


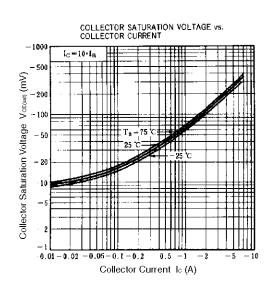


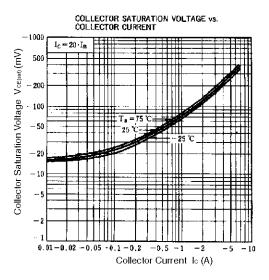




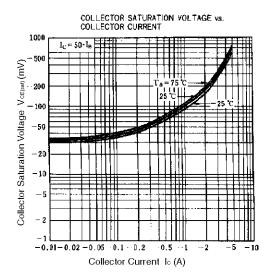


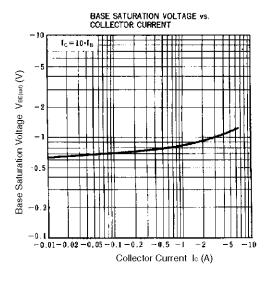


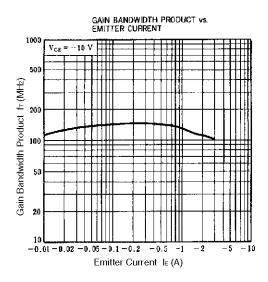


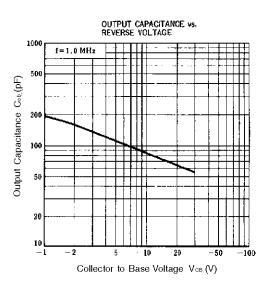


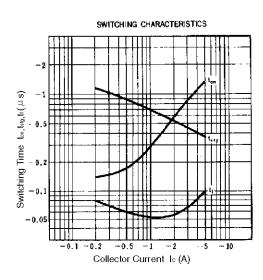
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[MEMO]

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